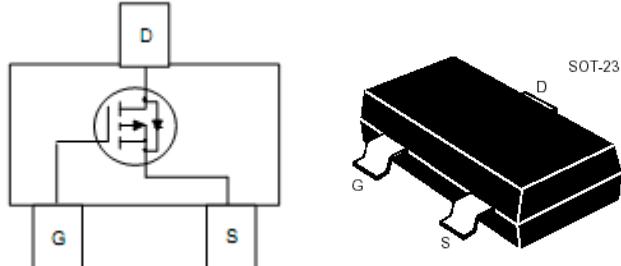


SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



P-Channel Enhancement-Mode MOS FETs

P 沟道增强型 MOS 场效应管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	-60	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 20	V
Drain Current (continuous) 漏極電流-連續	I_D	-1.8	A
Drain Current (pulsed) 漏極電流-脉沖	I_{DM}	-6	A
Total Device Dissipation 總耗散功率 $T_A=25^\circ\text{C}$ 環境溫度為 25°C	P_D	1000	mW
Junction 結溫	T_J	150	$^\circ\text{C}$
Storage Temperature 儲存溫度	T_{stg}	-55 to +150	$^\circ\text{C}$

■DEVICE MARKING 打標

GM2311-E11



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GM2311

■ELECTRICAL CHARACTERISTICS 電特性

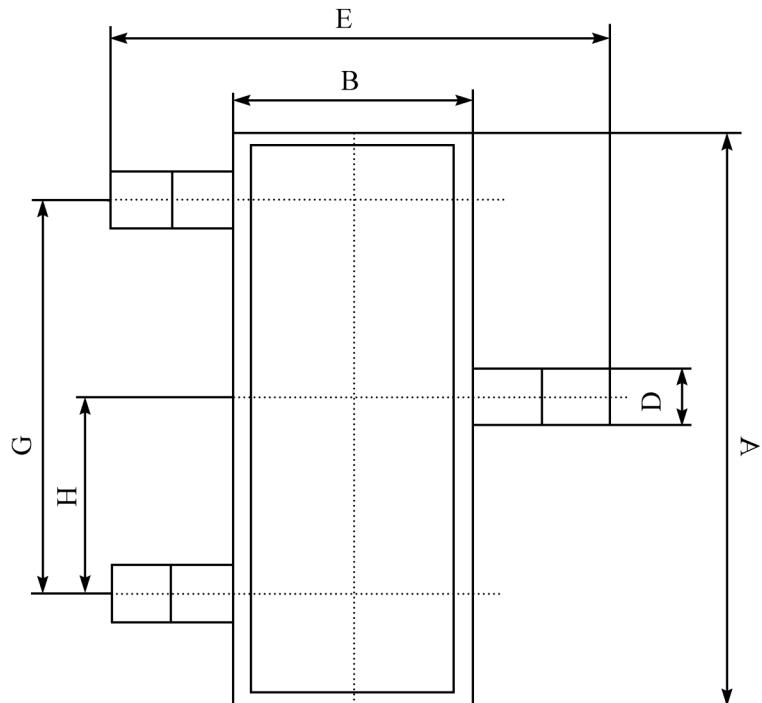
($T_A=25^\circ\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓($I_D = -250\mu\text{A}$, $V_{GS}=0\text{V}$)	BV_{DSS}	-60	—	—	V
Gate Threshold Voltage 柵極開啓電壓($I_D = -250\mu\text{A}$, $V_{GS}= V_{DS}$)	$V_{GS(\text{th})}$	-1	—	-3	V
Diode Forward Voltage Drop 內附二極管正向壓降($I_S = -1.2\text{A}$, $V_{GS}=0\text{V}$)	V_{SD}	—	—	-1.2	V
Zero Gate Voltage Drain Current 零柵壓漏極電流($V_{GS}=0\text{V}$, $V_{DS} = -60\text{V}$)	I_{DSS}	—	—	-10	μA
Gate Body Leakage 柵極漏電流($V_{GS}=\pm20\text{V}$, $V_{DS}=0\text{V}$)	I_{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D = -1.8\text{A}$, $V_{GS} = -10\text{V}$)	$R_{DS(\text{ON})}$	—	200	250	$\text{m}\Omega$
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D = -1.4\text{A}$, $V_{GS} = -4.5\text{V}$)	$R_{DS(\text{ON})}$	—	240	300	$\text{m}\Omega$
Input Capacitance 輸入電容 ($V_{GS}=0\text{V}$, $V_{DS} = -25\text{V}$, $f=1\text{MHz}$)	C_{ISS}	—	364	—	pF
Output Capacitance 輸出電容 ($V_{GS}=0\text{V}$, $V_{DS} = -25\text{V}$, $f=1\text{MHz}$)	C_{OSS}	—	41	—	pF
Turn-ON Time 开啓時間 ($V_{DS} = -30\text{V}$, $I_D = -1\text{A}$, $R_{GEN}=3.3\Omega$)	$t_{(\text{on})}$	—	20	—	ns
Turn-OFF Time 關斷時間 ($V_{DS} = -30\text{V}$, $I_D = -1\text{A}$, $R_{GEN}=3.3\Omega$)	$t_{(\text{off})}$	—	5.2	—	ns

Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$

DIMENSION 外形封装尺寸

單位(UNIT): mm



序號	數值及公差
A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	$0.00-0.10$
M	≥ 0.2
N	0.60 ± 0.10
P	$7 \pm 2^\circ$

